

IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

1-22 (Canceled)

23. (Currently amended) A method for assembling semiconductor devices, comprising:
providing a first semiconductor device;
placing discrete conductive elements over portions of the first semiconductor device; and
positioning a second semiconductor device at least partially over the first semiconductor device, a back side of the second semiconductor device resting upon at least some of the discrete conductive elements and being supported entirely thereby, the back side and the at least some of the discrete conductive elements being electrically isolated from each other.

24. (Currently amended) The method of claim 23, wherein the positioning the second semiconductor device comprises positioning the second semiconductor device on the at least some of the discrete conductive elements with the back side and the discrete conductive elements in mutual electrical isolation.

25. (Previously presented) The method of claim 24, further comprising:
providing a dielectric coating on at least portions of the discrete conductive elements.

26. (Previously presented) The method of claim 25, wherein the providing comprises forming at least one of a dielectric oxide and a dielectric polymer coating on the at least portions of the discrete conductive elements.

27. (Currently amended) The method of claim 24, wherein ~~the~~ positioning comprises positioning a dielectric layer on at least portions of the back side thereof.

28. (Canceled)

29. (Previously presented) The method of claim 23, further comprising: applying a quantity of adhesive material to at least an active surface of the first semiconductor device.

30. (Previously presented) The method of claim 29, further comprising: drawing the second semiconductor device toward the first semiconductor device.

31. (Currently amended) The method of claim 30, wherein ~~the~~ drawing is effected by at least one of capillary action of the adhesive material, curing of the adhesive material, application of heat to the adhesive material, and vibration of the adhesive material.

32. (Currently amended) The method of claim 29, wherein ~~the~~ applying includes applying the quantity of adhesive material to the back side of the second semiconductor device.

33. (Currently amended) The method of claim 29, wherein ~~the~~ applying is effected includes applying the quantity of adhesive material to at least the active surface of the first semiconductor device after the positioning the second semiconductor device.

34. (Previously presented) The method of claim 33, further comprising: drawing the second semiconductor device toward the first semiconductor device.

35. (Currently amended) The method of claim 34, wherein ~~the~~ drawing is effected during curing of the adhesive material.

36. (Currently amended) The method of claim 29, wherein ~~the~~ applying is effected before the positioning the second semiconductor device.

37. (Previously presented) The method of claim 36, further comprising: biasing at least one of the first and second semiconductor devices toward the other of the first and second semiconductor devices.

38. (Previously presented) The method of claim 37, further comprising: controlling the biasing.

39. (Currently amended) The method of claim 38, wherein ~~the~~ controlling the biasing comprises controlling biasing force to a level insufficient to deform, kink, bend, or collapse the discrete conductive elements.

40. (Previously presented) The method of claim 23, further comprising: securing the first semiconductor device and a substrate to one another.

41. (Currently amended) The method of claim 40, wherein ~~the~~ placing discrete conductive elements comprises securing the discrete conductive elements to contact areas of the substrate and bond pads of the first semiconductor device.

42. (Currently amended) The method of claim 41, wherein ~~the~~ securing comprises electrically connecting bond pads of the second semiconductor device to corresponding contact areas of the substrate.

43. (Previously presented) The method of claim 42, further comprising: encapsulating at least a portion of at least one of the substrate, the first semiconductor device, and the second semiconductor device.

44. (Previously presented) The method of claim 42, further comprising:
forming external conductive elements on the substrate in electrical communication with the
corresponding contact areas.

45. (Currently amended) A method for assembling semiconductor devices in a
stacked arrangement with the stacked arrangement having a height substantially equal to
combined thicknesses of each of the semiconductor devices and distances discrete conductive
elements associated therewith protrude above the each of the semiconductor devices, comprising:
providing a first semiconductor device with discrete conductive elements protruding from an
active surface thereof; and
positioning a second semiconductor device at least partially over the first semiconductor device
and on at least some discrete conductive elements of the discrete conductive elements
such that the second semiconductor device is entirely supported by the at least some
discrete conductive elements and the back side and the at least some discrete conductive
elements are electrically isolated from each other.

46. (Currently amended) The method of claim 45, wherein the positioning comprises
positioning the second semiconductor device on the at least some of the discrete conductive
elements with a back side of the second semiconductor device electrically isolated from the
discrete conductive elements.

47. (Previously presented) The method of claim 46, further comprising:
providing a dielectric coating on at least portions of the at least some of the discrete conductive
elements.

48. (Currently amended) The method of claim 46, wherein the positioning comprises
positioning a second semiconductor device that includes a dielectric coating on at least portions
of the back side thereof.

49. (Previously presented) The method of claim 45, further comprising: applying a quantity of adhesive material at least to the active surface of the first semiconductor device.

50. (Previously presented) The method of claim 49, further comprising: drawing the second semiconductor device toward the first semiconductor device.

51. (Currently amended) The method of claim 50, wherein the drawing is effected by at least one of capillary action of the adhesive material, curing of the adhesive material, application of heat to the adhesive material, and vibration of the adhesive material.

52. (Currently amended) The method of claim 49, wherein the applying is effected before the positioning the second semiconductor device.

53. (Currently amended presented) The method of claim 49, wherein the applying is effected after the positioning the second semiconductor device.

54. (Previously presented) The method of claim 53, further comprising: drawing the second semiconductor device toward the first semiconductor device.

55. (Currently amended) The method of claim 54, wherein the drawing is effected during curing of the adhesive material.

56. (Previously presented) The method of claim 49, further comprising: biasing at least one of the first and second semiconductor devices toward the other of the first and second semiconductor devices.

57. (Previously presented) The method of claim 56, further comprising: controlling the biasing.

58. (Currently amended) The method of claim 57, wherein the controlling the biasing comprises controlling biasing force to a level insufficient to deform, kink, bend, or collapse the discrete conductive elements.

59. (Previously presented) The method of claim 45, further comprising: positioning the first semiconductor device relative to a substrate.

60. (Previously presented) The method of claim 59, further comprising: connecting the discrete conductive elements to corresponding contact areas of the substrate.

61. (Previously presented) The method of claim 59, further comprising: establishing electrical communication between bond pads of the second semiconductor device and corresponding contact areas of the substrate.

62. (Currently amended) The method of claim 61, wherein the establishing communication comprises: placing additional discrete conductive elements between each of the bond pads and a corresponding contact area of the corresponding contact areas.

63. (Previously presented) The method of claim 46, further comprising: providing at least one external connective element in communication with at least one bond pad of each of the first and second semiconductor devices.

64. (Previously presented) The method of claim 63, further comprising: encapsulating at least portions of the first and second semiconductor devices.

65-69 (Canceled)